A 60 GHz 16 Gb/s 16QAM Low-Power Direct-Conversion Transceiver Using Capacitive Cross-Coupling Neutralization in 65 nm CMOS

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Abstract— This paper presents a 16QAM direct-conversion transceiver in 65 nm CMOS, which is capable of 60-GHz wireless standards. The capacitive cross-coupling neutralization contributes a high common-mode rejection and a high reverse isolation, and a fully-balanced mixer can improve the error vector magnitude due to the reduced local leakage. The maximum data rates with an antenna built in a package are 10 Gb/s in QPSK mode and 16 Gb/s in 16QAM mode and the transmitter and the receiver consume 181 mW and 138 mW, respectively.

I. INTRODUCTION

According to IEEE 802.15.3c standard, four 2.16GHzbandwidth channels are defined around the 60-GHz frequency, which are capable of achieving 3.5 Gb/s in QPSK and 7 Gb/s in 16QAM in raw data rate. This channel allocation is also common for IEEE 802.11ad, WiGig, WirelessHD, and ECMA standards. Recently, a couple of direct-conversion transceivers for the 60 GHz wireless communication have been reported[1], [2]. However, it is still difficult to realize the 16QAM direct-conversion even though 16QAM has to be supported for achieving a data rate of more than 5 Gb/s



Fig. 1. Block diagram of the 60 GHz direct-conversion transceiver.

within a limited frequency bandwidth[3], [4]. This paper proposes a fully-balanced direct-conversion tranceiver to improve modulation quality of 16QAM. The capacitive cross-coupling neutralization[5] is employed to achieve a high common-mode rejection and a high reverse isolation, and a fully-balanced mixer can improve the error vector magnitude due to the reduced local leakage. The following sections present detailed implementation and experimental results.

II. TRANSMITTER

Fig. 1 shows the entire block diagram of the proposed 60-GHz transceiver, and it has a direct-conversion architecture due to energy and area efficiency. The transmitter consists of a 3-stage PA, I/Q active mixers and a quadrature oscillator. The 3-stage PA has a single-ended configuration, and other parts have fully differential configurations. A low-loss transmission line, which has a loss of 0.8 dB/mm, is used for matching network, and the de-coupling is implemented with MIM transmission line(MIM TL). Transistors in the 3-stage PA have a finger width of $2 \mu m$, and the total gate width of the final stage is $80 \mu m$. A double-balanced Gilbert mixer is used, and Fig. 2 shows a circuit schematic of the mixer. The output is connected to the 3-stage PA through a parallel-line transformer



Fig. 2. Up-conversion mixer.



Fig. 3. Down-conversion mixer.

and a differential amplifier. The capacitive cross-coupling neutralization is applied to the differential amplifier. A crosscoupled capacitor between gate and drain of the oppositeside transistor cancels parasitic gate-to-drain capacitance and improves the reverse isolation. The high reverse isolation realizes high stability and gain enhancement. The common differential amplifier using a tail transistor cannot maintain a high CMRR at millimeter-wave frequency because of a parasitic capacitance at the drain of the tail transistor. Thus, the common-mode rejection is realized in the matching blocks of differential amplifiers. The shunt part in the matching blocks works as a short stub for a differential-mode signal because it forms a virtual ground. For a common-mode signal, it works as a open stub.

III. RECEIVER

The receiver design is shown in Figs. 3 and 4. The receiver consists of a 4-stage LNA, I/Q passive mixers, BB LNA, and a quadrature oscillator. The 4-stage LNA has a single-ended configuration and a CS-CS topology so that it improves the noise figure. Output of the LNA is connected to the passive mixer through the parallel-line transformer and a differential amplifier using the capacitive cross-coupling neutralization. A wideband low-noise BB LNA is used to compensate the conversion loss of the mixer, which is realized by a capacitive cross-coupled common-gate amplifier with a source-follower buffer.

IV. LOCAL OSCILLATOR

The LO consists of a quadrature injection-locked oscillator (QILO) and a 20 GHz PLL[6]. The QILO design is shown in Fig. 5. The QILO works as a frequency tripler with a 20 GHz injection-lock input, and it has a tail I/Q coupling, which is carefully designed to keep the I/Q balance robustly. Two quadrature oscillators are used, one for the transmitter and the other for the receiver, to maintain I/Q phase balance and avoid insertion loss in the 60 GHz LO distribution[7].

V. EXPERIMENTAL RESULTS

The transceiver is fabricated in 65 nm CMOS technology. The die photo is shown in Fig. 6. The core areas of TX



Fig. 4. BB LNA (capacitive cross-couple common-gate).



Fig. 5. Quadrature oscillator.

and RX are 2.5 mm^2 and 2.3 mm^2 , respectively. A post-wall waveguide antenna[8] is implemented in a package. It is connected with the CMOS chip through a $270 \,\mu\text{m}$ bonding wire. The antenna in the BGA package has a 2dBi gain. Fig. 7 shows the measured spectrum in QPSK mode with the IEEE802.15.3c spectrum mask. The measured spectrum meets the IEEE802.15.3c standard. An arbitrary waveform generator (AWG) generates I/Q modulated signals, and an oscilloscope is used to evaluate the constellation, EVM, and BER with a built-in software. The measured EVM is from 3.87 % (-28.2 dB) for 16QAM mode, which uses decision feedback equalization (DFE) realized by the built-in software.

Fig. 8 shows the conversion gain of TX, which is 16 dB. The large-signal measurement is calibrated with the saturated output power, which is measured by a probe station. Fig. 9 shows the measured output power, which is 5.4 dBm at 1-dB compression. The transmitter consumes 181 mW from a 1.2 V supply. Fig. 10 shows the conversion gain of RX. The LNA realizes a gain control, and the conversion gain is 27 dB in high-gain mode and 17 dB in low-gain mode. The lower cut-off frequency of the BB amplifier is less than 4MHz. Fig. 11 shows the noise figure. The entire noise figure is less than 6.1 dB, and the measured IIP3 is -20 dBm. The receiver consumes 138 mW from a 1.2 V supply. The measured free-running frequency is from 55-63 GHz. The overall phase noise is -94.2 dBc/Hz@1MHz-offset at 60.48GHz, which is measured through the entire TX path.





Tig. 8. Conversion gain of TA.

Table I shows the measured constellation. The symbol rate is 1.76 GS/s with a roll-off factor of 25 %, and the data rates with the 2.16 GHz bandwidth are 3.52 and 7.04 Gb/s for QPSK and 16QAM, respectively. The communication distances in QPSK and 16QAM modes are at least >100 cm



and >20 cm, respectively. The minimum BER in QPSK mode is also confirmed up to $<10^{-8}$ (limited by measurement time). Full-rate communication speed is possible for channel 1 (57.24 to 59.40 GHz) and channel 2 (59.40 to 61.56 GHz) of IEEE802.15.3c within a BER of $<10^{-3}$. The maximum data rates using wider bandwidth in QPSK and 16QAM with a 25% roll-off are at least 10 Gb/s and 16 Gb/s within a BER of $<10^{-3}$. BPSK and 8PSK can also be realized with the full data rates.

MEASURED CONSTELLATION FOR QPSK AND 16QAM. ٠ Constellation . . OPSK 16QAM OPSK Modulation **16QAM** Symbol rate 4.0GS/s 1.76GS/s 1.76GS/s 5.0GS/s Data rate 10.0Gb/s 3.52Gb/s 7.04Gb/s 16.0Gb/s EVM -16.1dB -30.5dB -28.2dB -15.2dB (withDFE)

TABLE I

VI. CONCLUSION

This paper presents a 60 GHz direct-conversion transceiver using the capacitive cross-coupling neutralization in 65 nm CMOS. A fully-balanced mixer is used to reduce the local leakage, and the matching blocks of differential amplifiers realize the common-mode rejection. The proposed transceiver realizes the 60 GHz wireless communication for 16QAM/8PSK/QPSK/BPSK mode, which is capable of channel 1 and channel 2 operation for the IEEE 802.15.3c standard. The maximum data rate is at least 10 Gb/s in QPSK mode and 16 Gb/s in 16QAM mode within a BER of $<10^{-3}$, and the transmitter and the receiver consume 181 mW and 138 mW, respectively.

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TABLE III Performance summary.

Тх		Rx		PLL		
CG	16 dB		17-27 dB	Frequency	17.9-21.2 GHz	
00	10 0.0	0	17-27 uD	Dhasa Maisa	0.4.2 dBc/Hz	
$P_{\rm 1dB}$	5.4 dBm	NF	< 6.1 dB	@60.48GHz	@1MHz-offset	
$\mathbf{P}_{\mathrm{sat}}$	6.5 dBm	IIP3	$-20\mathrm{dBm}$	P	-2 dBm	
P _{DC}	181 mW	P _{DC}	138 mW	P _D a	66 mW	
P _{DC}	181 mW	$P_{\rm DC}$	138 mW	PDC	66 mW	

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	Data rate/Modulation	EVM(16QAM)	Direct- Conversion	Integration	Power	Area				
[1]U. Toronto	4 Gb/s(BPSK)	N/A	Yes	65 nm, single-chip TRx w/o LO	374 mW with 1.2 V (233 mW with 1.0 V)	$1 \mathrm{mm}^2$				
[2]UCB	4 Gb/s(QPSK)	N/A	Yes	90 nm, single-chip TRx inc. 30GHz PLL with 90° hybrid and BB	170 mW(Tx mode) 138 mW(Rx mode)	6.8 mm ²				
[7]Tokyo Tech	8 Gb/s(QPSK) 11 Gb/s(16QAM)	$-17 dB \\ (Tx \rightarrow Rx)$	Yes	65 nm, single-chip TRx with 60 GHz quad. osc.	186 mW(Tx mode) 106 mW(Rx mode)	7.3 mm ² (TRx) 1.2 mm ² (PLL)				
[3]CEA-LETI	3.8 Gb/s(16QAM)	-20.7 dB (Tx) -19.2 dB (Rx)	No	65 nm, single-chip TRx with a HTCC package	1.357 W(Tx mode) 454 mW(Rx mode)	9.3 mm ² (TRx) 0.46 mm ² (PLL)				
[4]SiBeam	7.14 Gb/s(16QAM) 3.8 Gb/s(16QAM)	$-19.2 dB \\ (Tx \rightarrow Rx)$	No	65 nm, Tx/Rx with BB, maximum 32 sink/source phased-arrays	1.82 W(Tx mode) 1.25 W(Rx mode)	77.2 mm ² (Tx) 72.7 mm ² (Rx)				
This work	10 Gb/s(QPSK) 16 Gb/s(16QAM)	$-28.2 dB (Tx \rightarrow Rx)$	Yes	65 nm, single-chip, capacitive cross-coupled TRx with 60 GHz quad. osc.	181 mW(Tx mode) 138 mW(Rx mode)	4.8 mm ² (TRx) 1.2 mm ² (PLL)				

TABLE II Performance comparison.